TC74HC367AP/AF/AFN
TC74HC368AP/AF/AFN

HEX Bus Buffer
TC74HC367 Non-Inverted
TC74HC368 Inverted

The TC74HC367A and TC74HC368A are high speed CMOS 3-STATE BUFFERs fabricated with silicon gate C^2MOS technology.

They achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

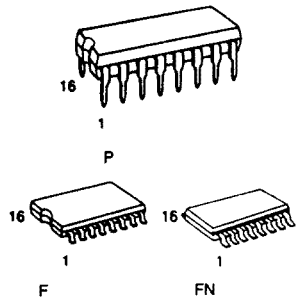
They contain six buffers; four buffers are controlled by an enable inputs ($\overline{G}1$), an the other two buffers are controlled by another enable input ($\overline{G}2$). The outputs of each buffer group are enabled when $\overline{G}1$ and/or $\overline{G}2$ inputs are held low; if held high, these outputs are in a high impedance state.

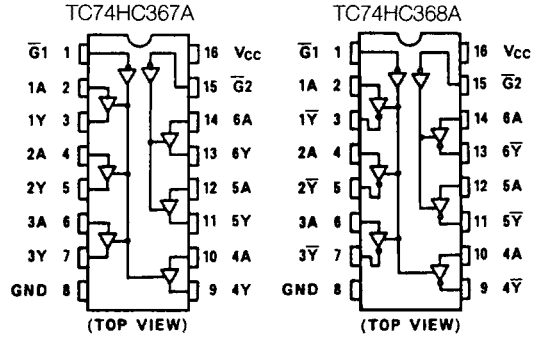
The TC74HC367A is an non-inverting output type, while the TC74HC368A is an inverting output type.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

Features

- High Speed: t_{pd} = 11ns(Typ.) at V_{CC} = 5V
- Low Power Dissipation: I_{CC} = 4μA(Max.) at Ta = 25°C
- High Noise Immunity: $V_{NIH} = V_{NIL}$ = 28% V_{CC}(Min.)
- Output Drive Capability: 15 LSTTL Loads
- Symmetrical Output Impedance: $|I_{OH}| = I_{OL}$ = 6mA(Min.)
- Balanced Propagation Delays: $t_{pLH} = t_{pHL}$
- Wide Operating Voltage Range: V_{CC}(opr) = 2V ~ 6V
- Pin and Function Compatible with 74LS367/368



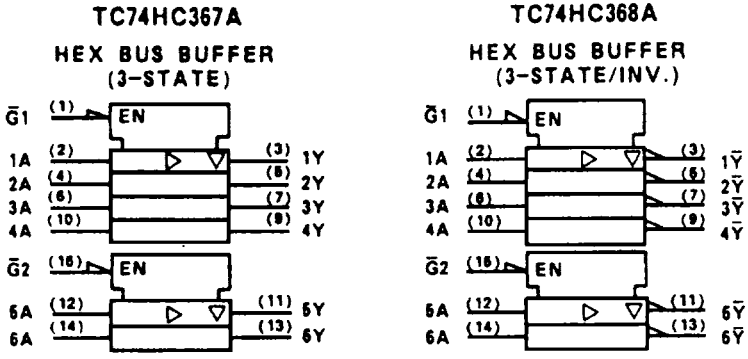


Pin Assignment

Truth Table

Inputs		Outputs	
$\overline{G}$	An	Yn(367A)	$\overline{Y}$n(368A)
L	L	L	H
L	H	H	L
H	X	Z	Z

X: Don't Care
Z: High Impedance



IEC Logic Symbol

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Supply Voltage Range	V_{CC}	-0.5 ~ 7	V
DC Input Voltage	V_{IN}	-0.5 ~ V_{CC} + 0.5	V
DC Output Voltage	V_{OUT}	-0.5 ~ V_{CC} + 0.5	V
Input Diode Current	I_{IK}	±20	mA
Output Diode Current	I_{OK}	±20	mA
DC Output Current	I_{OUT}	±35	mA
DC V_{CC}/Ground Current	I_{CC}	±75	mA
Power Dissipation	P_D	500(DIP)*/180(MFP)	mW
Storage Temperature	T_{stg}	-65 ~ 150	°C
Lead Temperature 10sec	T_L	300	°C

*500mW in the range of Ta = -40°C ~ 65°C. From Ta = 65°C to 85°C a derating factor of -10mW/°C shall be applied until 300mW.

Recommended Operating Conditions

Parameter	Symbol	Value	Unit
Supply Voltage	V_{CC}	2 ~ 6	V
Input Voltage	V_{IN}	0 ~ V_{CC}	V
Output Voltage	V_{OUT}	0 ~ V_{CC}	V
Operating Temperature	T_{opr}	-40 ~ 85	°C
Input Rise and Fall Time	t_r, t_f	0 ~ 1000(V_{CC} = 2.0V) 0 ~ 500(V_{CC} = 4.5V) 0 ~ 400(V_{CC} = 6.0V)	ns

DC Electrical Characteristics

Parameter	Symbol	Test Condition		V_{CC}	Ta = 25°C Min.	Ta = 25°C Typ.	Ta = 25°C Max.	Ta = -40 ~ 85°C Min.	Ta = -40 ~ 85°C Max.	Unit
High-Level Input Voltage	V_{IH}	–		2.0 4.5 6.0	1.5 3.15 4.2	– – –	– – –	1.5 3.15 4.2	– – –	V
Low-Level Input Voltage	V_{IL}	–		2.0 4.5 6.0	– – –	– – –	0.5 1.35 1.8	– – –	0.5 1.35 1.8	V
High-Level Output Voltage	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = -20μA	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0	– – –	1.9 4.4 5.9	– – –	V
			I_{OH} = -6 mA I_{OH} = -7.8mA	4.5 6.0	4.18 5.68	4.31 5.80	– –	4.13 5.63	– –	
Low-Level Output Voltage	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 20μA	2.0 4.5 6.0	– – –	0.0 0.0 0.0	0.1 0.1 0.1	– – –	0.1 0.1 0.1	V
			I_{OL} = 6 mA I_{OL} = 7.8mA	4.5 6.0	– –	0.17 0.18	0.26 0.26	– –	0.33 0.33	
3-State Output Off-State Current	I_{OZ}	V_{IN} = V_{IH} or V_{IL} V_{OUT} = V_{CC} or GND		6.0	–	–	±0.5	–	±5.0	μA
Input Leakage Current	I_{IN}	V_{IN} = V_{CC} or GND		6.0	–	–	±0.1	–	±1.0	
Quiescent Supply Current	I_{CC}	V_{IN} = V_{CC} or GND		6.0	–	–	4.0	–	40.0	

AC Electrical Characteristics (Input $t_r = t_f = 6ns$)

Parameter	Symbol	Test Condition			Ta = 25°C			Ta = -40 ~ 85°C		Unit
			CL	V_{CC}	Min.	Typ.	Max.	Min.	Max.	
Output Transition Time	t_{TLH} t_{THL}	–	50	2.0 4.5 6.0	– – –	25 7 6	60 12 10	– – –	75 15 13	ns
Propagation Delay Time	t_{pLH} t_{pHL}	–	50	2.0 4.5 6.0	– – –	36 12 10	95 19 16	– – –	120 24 20	
			150	2.0 4.5 6.0	– – –	40 16 14	130 26 22	– – –	165 33 28	
Output Enable Time	t_{pZL} t_{pZH}	$R_L = 1K\Omega$	50	2.0 4.5 6.0	– – –	36 12 10	120 24 20	– – –	150 30 26	
			150	2.0 4.5 6.0	– – –	40 16 14	160 32 27	– – –	200 40 34	
Output Disable Time	t_{pLZ} t_{pHZ}	$R_L = 1K\Omega$	50	2.0 4.5 6.0	– – –	35 15 13	120 24 20	– – –	150 30 26	
Input Capacitance	C_{IN}	–			–	5	10	–	10	pF
Output Capacitance	C_{OUT}	–			–	10	–	–	–	
Power Dissipation Capacitance	C_{PD}(1)	TC74HC367A			–	36	–	–	–	
		TC74HC368A			–	30	–	–	–	

Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:
$I_{CC(opr)} = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}/6$(per bit)